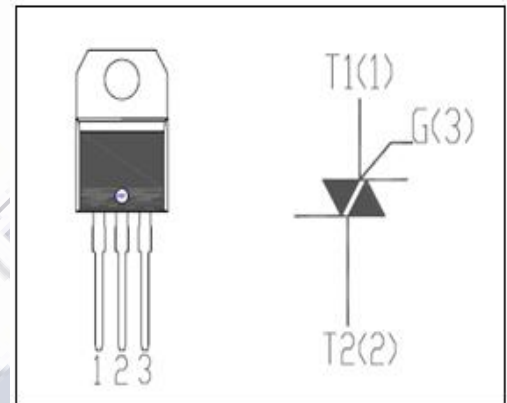


isc Thyristors
BTA26-800B
DESCRIPTION

- With TO-3PN packaging
- Operating in 4 quadrants
- High voltage capability;high current capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Applications subject to high temperature
- Heating controls; high power motor control
- High power switching


ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	MAX	UNIT
V _{DRM}	Repetitive peak off-state voltage	800	V
V _{RPM}	Repetitive peak reverse voltage	800	V
I _{T(RSM)}	RSM average on-state current	T _c =90°C	25
I _{TSM}	Surge non-repetitive on-state current	50HZ 60HZ	250 260
P _{G(AV)}	Average gate power dissipation (over any 20 ms period) @ T _c =125°C		1
T _j	Operating junction temperature	-40~125	°C
T _{stg}	Storage temperature	-40~150	°C

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _R =V _{RRM} Rated; T _j =25°C		5	μ A
I _{DRM}	Repetitive peak off-state current	V _D =V _{DRM} Rated; T _j =125°C		3	mA
V _{TM}	On-state voltage	I _T =35A;t _p =380 μ s		1.55	V
I _{GT}	Gate-trigger current	V _D =12V;R _L =33Ω;	I II III IV	50 50 50 100	mA
V _{GT}	Gate-trigger voltage	V _D =12V;R _L =33Ω;		1.3	V
R _{th(j-c)}	Junction to case			1.1	°C/W